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<u>Diodes Incorporated</u> ZXMP10A17E6QTA

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Datasheet of ZXMP10A17E6QTA - MOSFET P-CH 100V 1.3A SOT23-6

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ZXMP10A17E6Q

#### 100V P-CHANNEL ENHANCEMENT MODE MOSFET

### **Product Summary**

V <sub>(BR)DSS</sub>	R <sub>DS(ON)</sub>	I <sub>D</sub> T <sub>A</sub> = +25°C
-100V	350mΩ @ V <sub>GS</sub> = -10V	-1.6A
-1007	450mΩ @ V <sub>GS</sub> = -6.0V	-1.4A

#### **Description**

This MOSFET is designed to minimize the on-state resistance and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

## **Applications**

- Motor Control
- DC-DC Converters
- Power Management Functions
- Uninterrupted Power Supply

## **Features and Benefits**

- Fast Switching Speed
- Low Gate Drive
- Low Input Capacitance
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

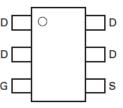
#### **Mechanical Data**

- Case: SOT26
- Case Material: Molded Plastic, "Green" Molding Compound; UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals Connections: See Diagram Below
- Terminals: Finish Matte Tin Annealed over Copper Leadframe; Solderable per MIL-STD-202, Method 208
- Weight: 0.018 grams (Approximate)

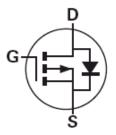




Top View



Pin Out - Top View



Equivalent Circuit

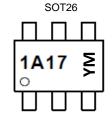
#### Ordering Information (Notes 4 & 5)

Part Number	Qualification	Case	Packaging	
ZXMP10A17E6QTA	Automotive	SOT26	3,000/Tape & Reel	

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified. For more information, please refer to http://www.diodes.com/quality/product\_compliance\_definitions/.
- 5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

#### **Marking Information**



1A17 = Product Type Marking Code YM = Date Code Marking Y or  $\overline{Y}$  = Year (ex: C = 2015) M or  $\overline{M}$  = Month (ex: 9 = September)

#### Date Code Key

	,												
Yea	ar	2015	2016	2017	2018	2019	2020	2021	2022	2023	2024	2025	2026
Cod	de	С	D	Е	F	G	Н	- 1	J	K	L	М	N

			Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code 1	2	3	4	5	6	7	8	9	0	N	D

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#### **Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

	haracteristic		Symbol	Value	Unit
Drain-Source Voltage			V <sub>DSS</sub>	-100	V
Gate-Source Voltage			V <sub>GS</sub>	±20	V
		(Note 7)		-1.6	
Continuous Drain Current	$V_{GS} = 10V$	$T_A = +70^{\circ}C \text{ (Note 7)}$	I <sub>D</sub>	-1.3	Α
		(Note 6)		-1.3	
Pulsed Drain Current	V <sub>GS</sub> = 10V	(Note 8)	I <sub>DM</sub>	-7.7	А
Continuous Source Current (Body Diode) (Note 7)			Is	-2.1	А
Pulsed Source Current (Bod	y Diode)	(Note 8)	I <sub>SM</sub>	-7.7	А

#### Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Power Dissipation	(Note 6)		1.1 8.8	W	
Linear Derating Factor	(Note 7)	PD	1.7 13.7	mW/°C	
Thermal Peciatones, Junction to Ambient	(Note 6)	D	113	°C/W	
Thermal Resistance, Junction to Ambient	(Note 7)	R <sub>θJA</sub>	73	- C/VV	
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C		

#### Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS			•	•	•		
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-100	_	_	V	$I_D = -250 \mu A, V_{GS} = 0 V$	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	_	_	-0.5	μΑ	$V_{DS} = -100V, V_{GS} = 0V$	
Gate-Source Leakage	I <sub>GSS</sub>	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS			•	•	•		
Gate Threshold Voltage	V <sub>GS(TH)</sub>	-2.0	_	-4.0	V	$I_D = -250 \mu A$ , $V_{DS} = V_{GS}$	
Static Drain-Source On-Resistance (Note 9)	D			0.350	Ω	$V_{GS} = -10V, I_D = -1.4A$	
Static Dialii-Source Off-Resistance (Note 9)	R <sub>DS(ON)</sub>	_		0.450	122	$V_{GS} = -6V, I_D = -1.2A$	
Forward Transconductance (Notes 9 & 10)	<b>g</b> fs	_	2.8	_	S	V <sub>DS</sub> = -15V, I <sub>D</sub> = -1.4A	
Diode Forward Voltage (Note 9)	$V_{SD}$	_	-0.85	-0.95	V	I <sub>S</sub> = -1.7A, V <sub>GS</sub> = 0V	
Reverse Recovery Time (Note 10)	t <sub>rr</sub>	_	33	_	ns	I <sub>S</sub> = -1.5A, di/dt = 100A/µs	
Reverse Recovery Charge (Note 10)	Qrr	_	48	_	nC	-1/S = -1:5A, α//αι = 100A/μS	
DYNAMIC CHARACTERISTICS (Note 10)							
Input Capacitance	Ciss	_	424	_	pF	\(\(\text{50\}\)\\\	
Output Capacitance	Coss	_	36.6	_	pF	$V_{DS} = -50V, V_{GS} = 0V$ - f = 1MHz	
Reverse Transfer Capacitance	C <sub>rss</sub>	_	29.8	_	pF	7 - 11/11/2	
Total Gate Charge (Note 11)	Qg	_	7.1	_	nC	V <sub>GS</sub> = -6V	
Total Gate Charge (Note 11)	$Q_g$	_	10.7	_	nC	V <sub>DS</sub> = -50V	
Gate-Source Charge (Note 11)	Qgs	_	1.7	_	nC	$V_{GS} = -10V$ $I_{D} = -1.4A$	
Gate-Drain Charge (Note 11)	$Q_{gd}$	_	3.8	_	nC	]	
Turn-On Delay Time (Note 11)	t <sub>D(on)</sub>	_	3	_	ns		
Turn-On Rise Time (Note 11)	t <sub>r</sub>	_	3.5	_	ns	V <sub>DD</sub> = -50V, V <sub>GS</sub> = -10V	
Turn-Off Delay Time (Note 11)	t <sub>D(off)</sub>	_	13.4	_	ns	$I_D = -1A, R_G \cong 6.0\Omega$	
Turn-Off Fall Time (Note 11)	t <sub>f</sub>	_	7.2	_	ns	1	

Notes:

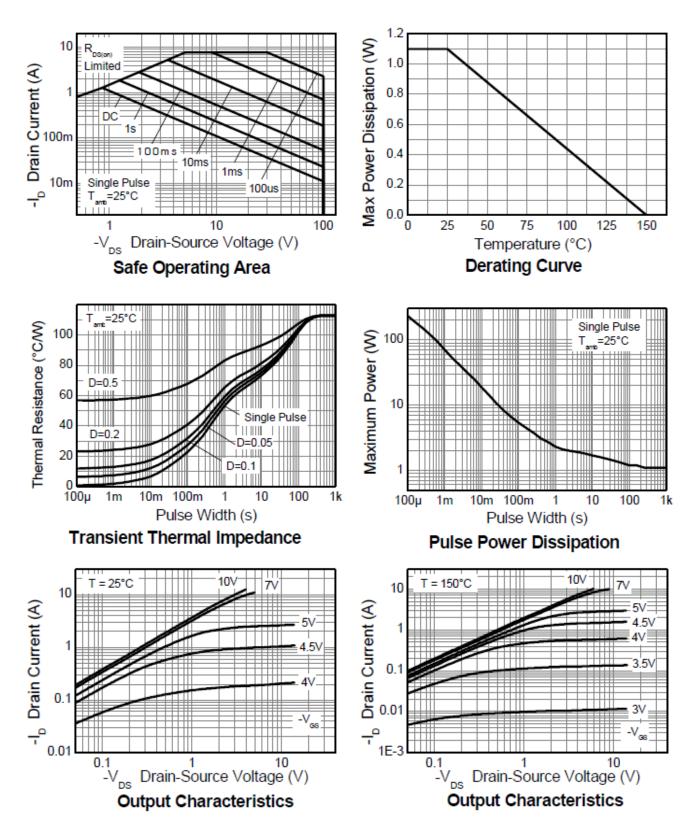
- 6. For a device surface mounted on 25mm x 25mm FR-4 PCB with high coverage of single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
- 7. Same as Note 6, except the device is measured at  $t\ \leq 5$  sec.
- 8. Same as Note 6, except the device is pulsed with D = 0.05 and pulse width 10µs. The pulse current is limited by the maximum junction temperature.

- 9. Measured under pulsed conditions. Pulse width  $\leq$  300 $\mu$ s; duty cycle  $\leq$  2%. 10. For design aid only, not subject to production testing. 11. Switching characteristics are independent of operating junction temperatures.





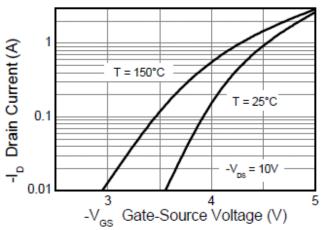
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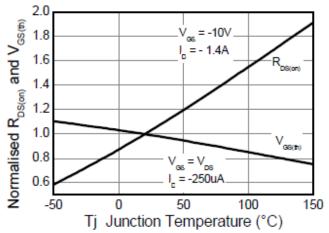






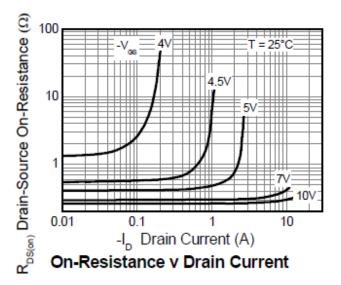
## ZXMP10A17E6Q

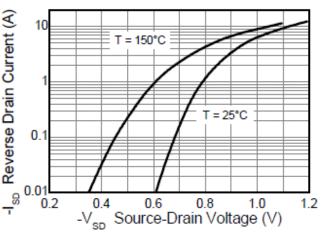




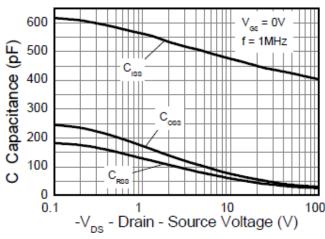
**Typical Transfer Characteristics** 

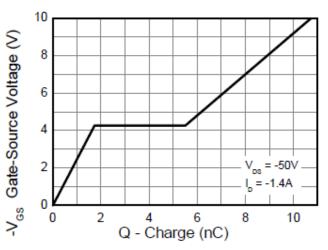
Normalised Curves v Temperature





Source-Drain Diode Forward Voltage





Capacitance v Drain-Source Voltage

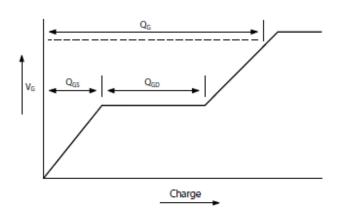
Gate-Source Voltage v Gate Charge



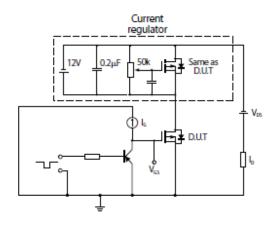


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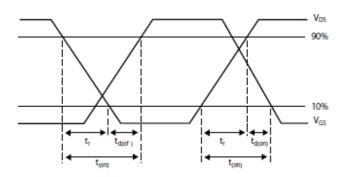
## **Test Circuits**



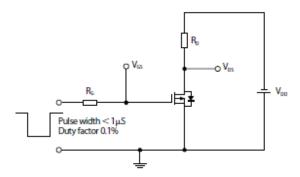
Basic gate charge waveform



Gate charge test circuit



Switching time waveforms



Switching time test circuit

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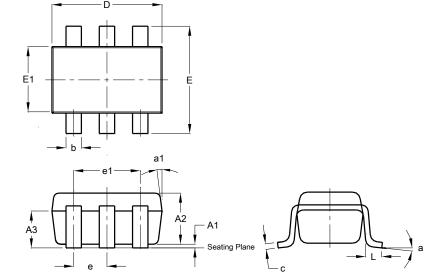
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## **Package Outline Dimensions**

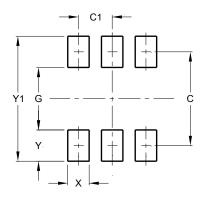
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



SOT26							
Dim	Min	Max	Тур				
A1	0.013	0.10	0.05				
A2	1.00	1.30	1.10				
A3	0.70	0.80	0.75				
b	0.35	0.50	0.38				
С	0.10	0.20	0.15				
D	2.90 3.10		3.00				
е	-	-	0.95				
e1	-		1.90				
Е	2.70	3.00	2.80				
E1	1.50	1.70	1.60				
L	0.35	0.55	0.40				
а	-	-	8°				
a1	-		7°				
All	Dimen	sions	in mm				

## **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
С	2.40
C1	0.95
G	1.60
Х	0.55
Υ	0.80
Y1	3.20



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